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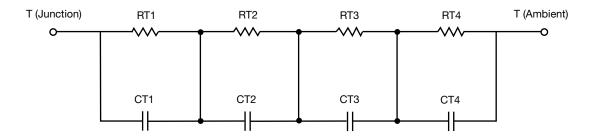
## **R-C Thermal Model Parameters**

#### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK	CONFIGURATION		
	THERMAL RES	SISTANCE (°C/W)	
Junction to	Ambient	Case	Foot
RT1	n/a	10.4347m	n/a
RT2	n/a	225.6848m	n/a
RT3	n/a	223.0263m	n/a
RT4	n/a	240.8542m	n/a
	THERMAL CAPAC	CITANCE (Joules/°C)	
Junction to	Ambient	Case	Foot
CT1	n/a	5.3933m	n/a
CT2	n/a	16.6921m	n/a
CT3	n/a	21.0152m	n/a
CT4	n/a	141.9274m	n/a

#### Note

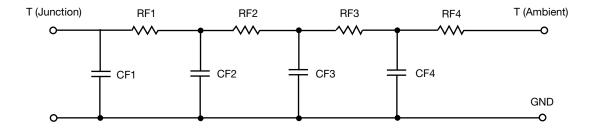
n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	314.1825m	n/a		
RF2	n/a	133.7599m	n/a		
RF3	n/a	78.6559m	n/a		
RF4	n/a	173.4017m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	7.6700m	n/a		
CF2	n/a	2.2571m	n/a		
CF3	n/a	15.5739m	n/a		
CF4	n/a	164.8937m	n/a		

#### Note

• n/a indicates not applicable





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